

N-channel 100 V 3.9 mΩ standard level MOSFET in D2PAK Rev. 2 — 29 February 2012 Product data s

Product data sheet

#### **Product profile** 1.

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### 1.1 General description

Standard level N-channel MOSFET in a D2PAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

### 1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

### 1.4 Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	100	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>	<u>[1]</u> _	-	120	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	306	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5.9	6.9	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	3.28	3.9	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 10 V; $I_{D}$ = 75 A; $V_{DS}$ = 50 V;	-	49	-	nC
Q <sub>G(tot)</sub>	total gate charge	see Figure 14; see Figure 15	-	170	-	nC
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$      V_{GS} = 10 \text{ V};  \text{T}_{j(init)} = 25 \text{ °C};  \text{I}_{\text{D}} = 120 \text{ A}; \\       V_{sup} \leq 100 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \text{ Unclamped} $	-	-	537	mJ

[1] Continuous current is limited by package.

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#### N-channel 100 V 3.9 m $\Omega$ standard level MOSFET in D2PAK

### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain <sup>[1]</sup>	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT404 (D2PAK)	

[1] It is not possible to make connection to pin 2.

### 3. Ordering information

### Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN3R8-100BS	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

### 4. Limiting values

#### Table 4. Limiting values

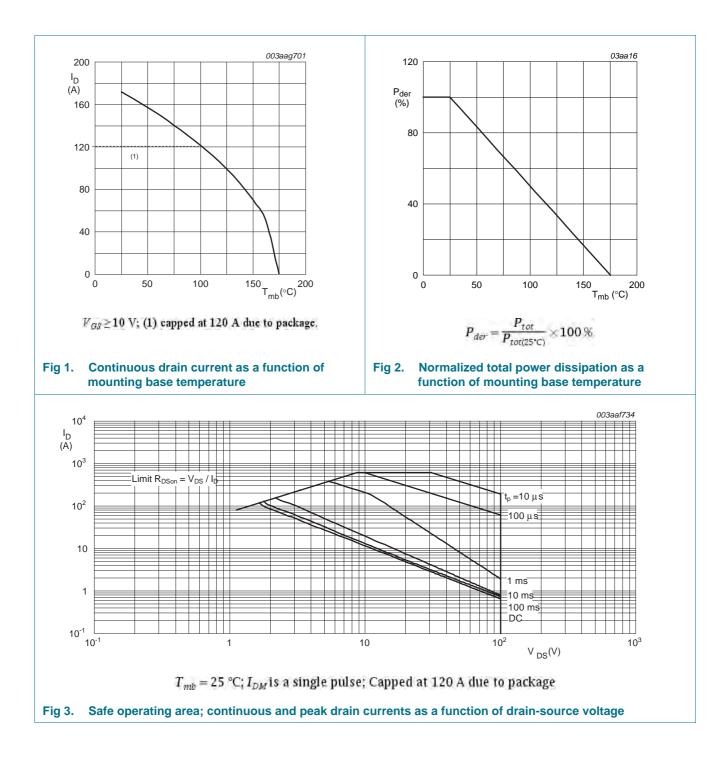
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	100	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; T <sub>j</sub> = 100 °C; see <u>Figure 1</u>	<u>[1]</u> _	120	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	<u>[1]</u> _	120	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; see Figure 3	-	680	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	306	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature		-	260	°C
Source-drain	diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	<u>[1]</u> _	120	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	680	А
Avalanche rug	ggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; $I_D$ = 120 A; $V_{sup} \le 100$ V; $R_{GS}$ = 50 $\Omega$ ; Unclamped	-	537	mJ

[1] Continuous current is limited by package.

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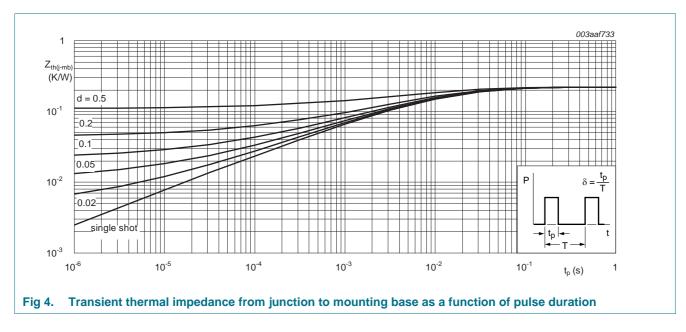
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### N-channel 100 V 3.9 m $\Omega$ standard level MOSFET in D2PAK

### 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	see Figure 4	-	0.22	0.49	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	minimum footprint; mounted on a printed-circuit board	-	50	-	K/W



#### Table 5. Thermal characteristics

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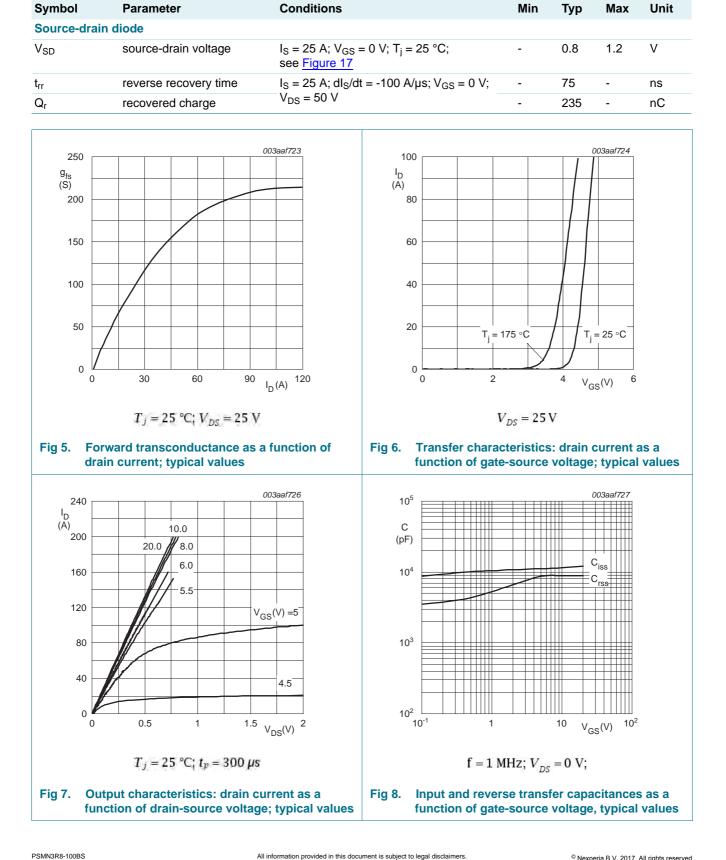
### N-channel 100 V 3.9 mΩ standard level MOSFET in D2PAK

### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	100	-	-	V
	voltage	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ C$	90	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u>	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see Figure 11; see Figure 10	2	3	4	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.08	10	μA
		V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	250	500	μA
IGSS	gate leakage current	V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	10	100	nA
		V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	10	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 175 °C; see Figure 12; see Figure 13	-	9	10.6	mΩ
		$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 100 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5.9	6.9	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_{D} = 25 \text{ A}; \text{ T}_{j} = 25 \text{ °C};$ see Figure 12; see Figure 13	-	3.28	3.9	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.9	-	Ω
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	170	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	140	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 15; see Figure 14	-	48	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	$I_D = 75 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14; see Figure 15	-	31	-	nC
Q <sub>GS(th</sub> -pl)	post-threshold gate-source charge		-	17.3	-	nC
Q <sub>GD</sub>	gate-drain charge		-	49	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 50 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	5.1	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	9900	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 16}{100}$	-	660	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	381	-	pF
d(on)	turn-on delay time	$V_{DS}$ = 50 V; $R_{L}$ = 0.67 Ω; $V_{GS}$ = 10 V;	-	45	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \ \Omega; \ I_D = 75 \ A; \ T_j = 25 \ ^{\circ}C$	-	91	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	122	-	ns
t <sub>f</sub>	fall time		-	63	-	ns

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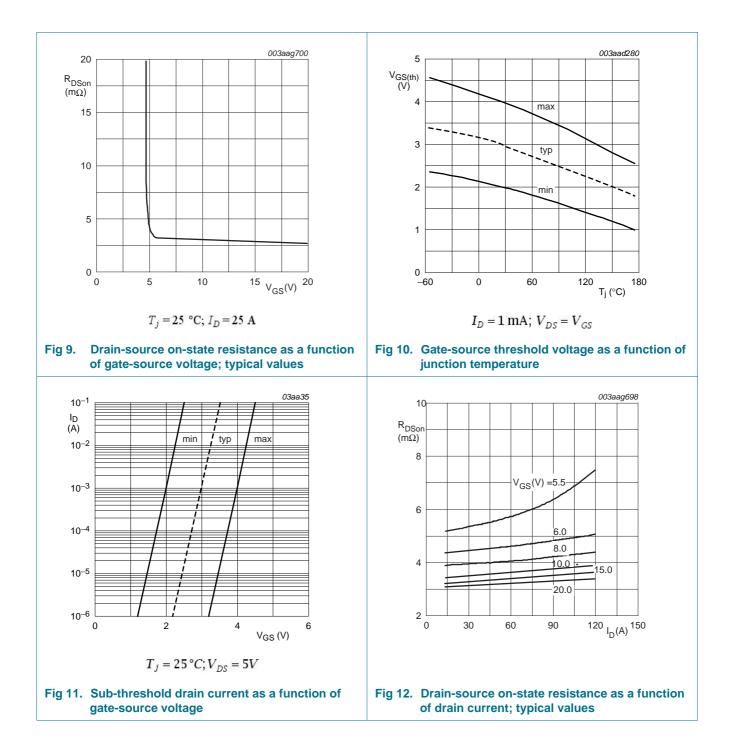
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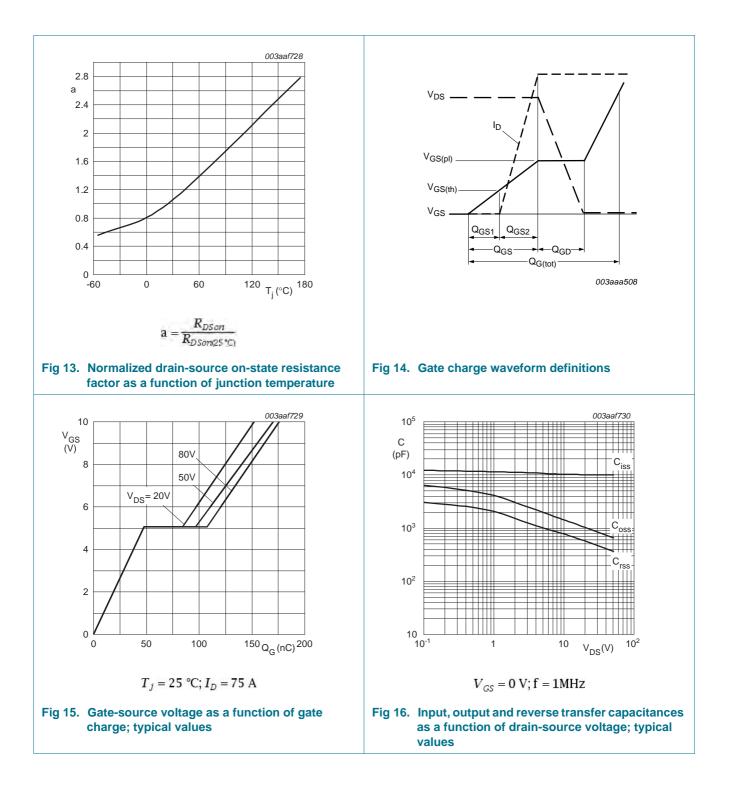
#### Table 6. Characteristics ...continued

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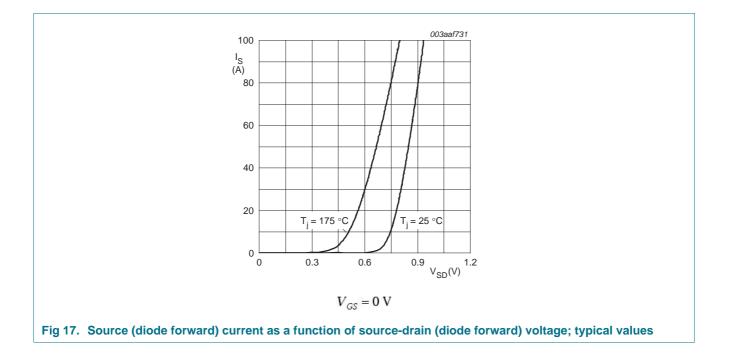
# PSMN3R8-100BS



# PSMN3R8-100BS

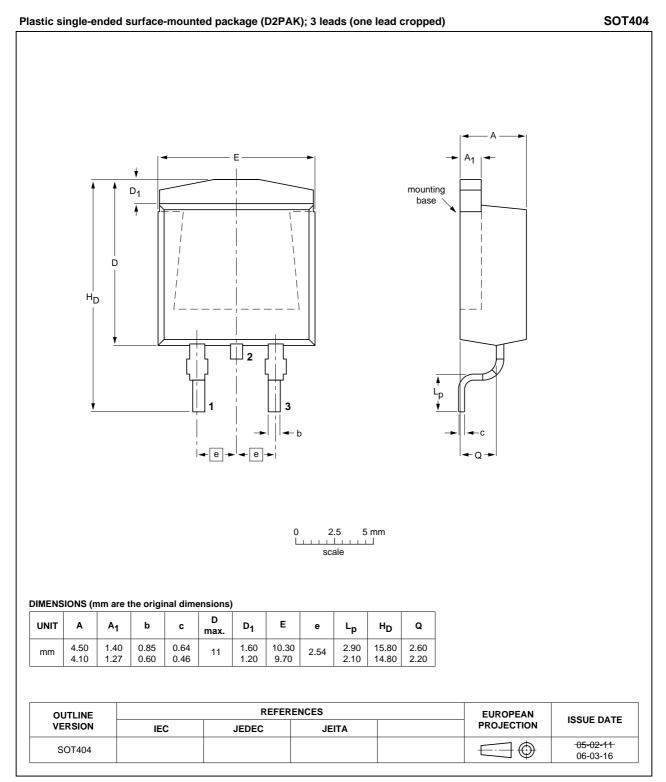


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#### N-channel 100 V 3.9 mΩ standard level MOSFET in D2PAK

### 7. Package outline



#### Fig 18. Package outline SOT404 (D2PAK)

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### N-channel 100 V 3.9 mΩ standard level MOSFET in D2PAK

### 8. Revision history

Table 7. Revision history	able 7.	<b>Revision history</b>
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Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN3R8-100BS v.2	20120229	Product data sheet	-	PSMN3R8-100BS v.1
Modifications:	Status changed	from objective to product.		
	<ul> <li>Various changes</li> </ul>	s to content.		
PSMN3R8-100BS v.1	20110829	Objective data sheet	-	-

### 9. Legal information

### 9.1 Data sheet status

Document status[1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Product data sheet

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### N-channel 100 V 3.9 mΩ standard level MOSFET in D2PAK

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